

Data Sheet October 2003 FN4560.7

Radiation Hardened Adjustable Positive Voltage Regulator

The Radiation Hardened HS-117RH is an adjustable positive voltage linear regulator capable of operating with input voltages up to 40VDC. The output voltage is adjustable from 1.2V to 37V with two external resistors. The device is capable of sourcing from 5mA to 1.25APEAK (0.5 APEAK for the TO-39 package). Protection is provided by the on-chip thermal shutdown and output current limiting circuitry.

The Intersil HS-117RH has advantages over other industry standard types, in that circuitry is incorporated to minimize the effects of radiation and temperature on device stability.

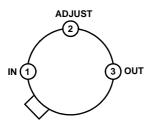
Constructed with the Intersil dielectrically isolated Rad Hard Silicon Gate (RSG) process, the HS-117RH is immune to single event latch-up and has been specifically designed to provide highly reliable performance in harsh radiation environments.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed here must be used when ordering.

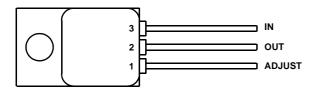
Detailed electrical specifications for the HS-117RH are contained in SMD 5962-99547. A "hot-link" is provided on our website for downloading.

Pinouts

HS2-117RH (TO-39 CAN) BOTTOM VIEW



HS9S-117RH (TO-257AA FLANGE MOUNT) TOP VIEW



Features

- Electrically Screened to DSSC SMD # 5962-99547
- QML Qualified per MIL-PRF-38535 Requirements
- · Radiation Environment
 - 300 krad (Si) (Max)
 - Latch-up Immune
- · Superior Temperature Stability
- · Overcurrent and Overtemperature Protection

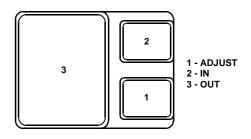
Applications

- · Adjustable Linear Voltage Regulators
- · Adjustable Linear Current Regulators

Ordering Information

INTERNAL MKT. NUMBER	TEMP. RANGE (°C)
HS2-117RH-Q	-55 to 125
HS2-117RH-8	-55 to 125
HS9S-117RH-Q	-55 to 125
HS9S-117RH-8	-55 to 125
HSYE-117RH-Q	-55 to 125
HSYE-117RH-8	-55 to 125
HS2-117RH/Proto	-55 to 125
HS9S-117RH/Proto	-55 to 125
HSYE-117RH/Proto	-55 to 125
	MKT. NUMBER HS2-117RH-Q HS2-117RH-8 HS9S-117RH-Q HS9S-117RH-8 HSYE-117RH-Q HSYE-117RH-8 HS2-117RH/Proto HS9S-117RH/Proto

HSYE-117RH (SMD.5 CLCC) BOTTOM VIEW



NOTE: No current JEDEC outline for the SMD.5 package. Refer to SMD for package dimensions. The TO-257 is a totally isolated metal package.

HS-117RH

Die Characteristics

DIE DIMENSIONS

 $2616\mu m$ x $2794\mu m$ (103 mils x 110 mils) $483\mu m$ $\pm 25.4\mu m$ (19 mils ± 1 mil)

INTERFACE MATERIALS

Glassivation

Type: Silox (SiO₂) Thickness: $8.0kÅ \pm 1.0kÅ$

Top Metallization

Type: AlSiCu

Thickness: 16.0kÅ ±2kÅ

Substrate

Radiation Hardened Silicon Gate, Dielectric Isolation

Backside Finish

Gold

ASSEMBLY RELATED INFORMATION

Substrate Potential

Unbiased (DI)

ADDITIONAL INFORMATION

Worst Case Current Density

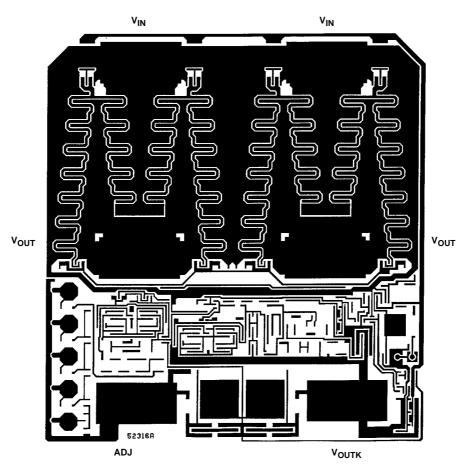
 $< 2.0 \times 10^5 \text{ A/cm}^2$

Transistor Count

95

Metallization Mask Layout

HS-117RH



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